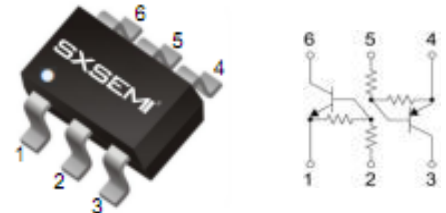


FEATURES

- DTA114E and DTC114E transistors are built-in a package.
- Transistor elements are independent, eliminating interference.

SOT-363



MARKING:D3

Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limit	Unit
Supply voltage	V_{CC}	50	V
Input voltage	V_{IN}	-10~40	V
Output current	I_O	50	mA
	$I_{C(MAX)}$	100	
Power dissipation	P_D^*	150	mW
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

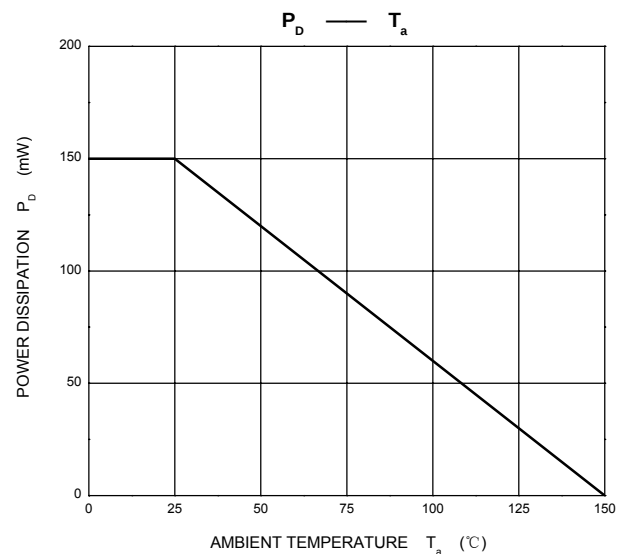
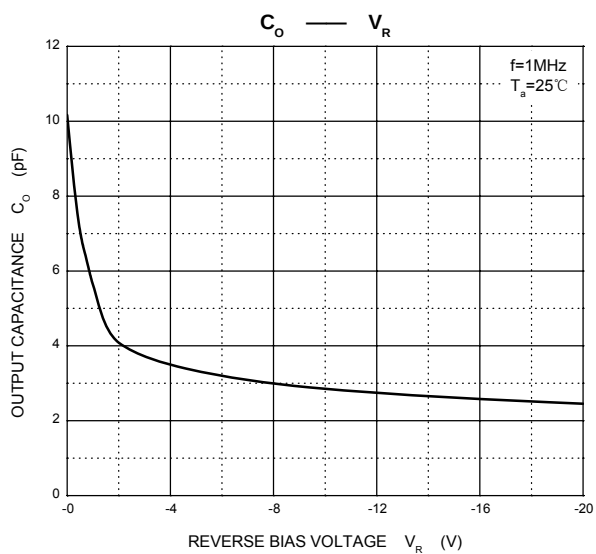
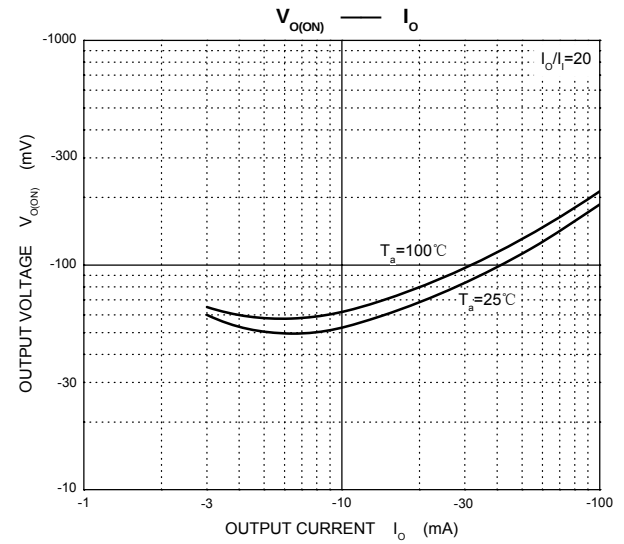
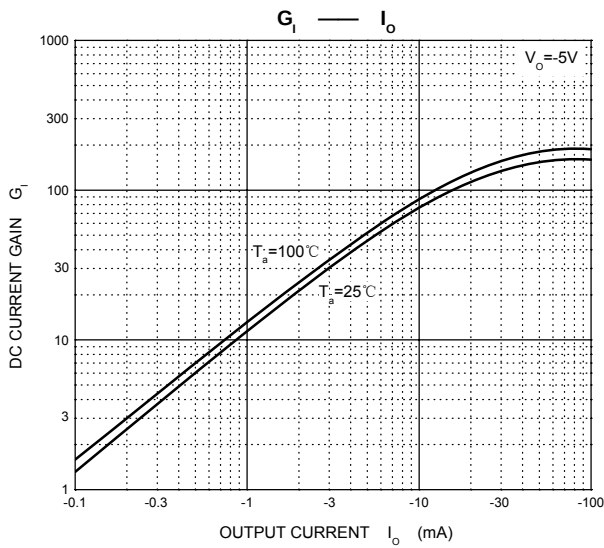
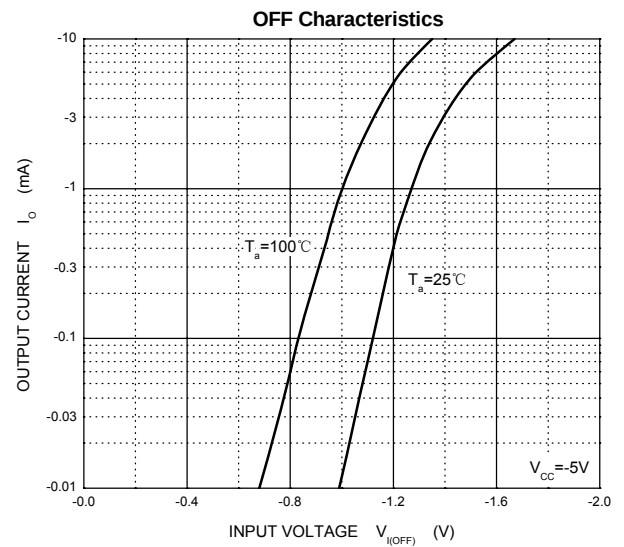
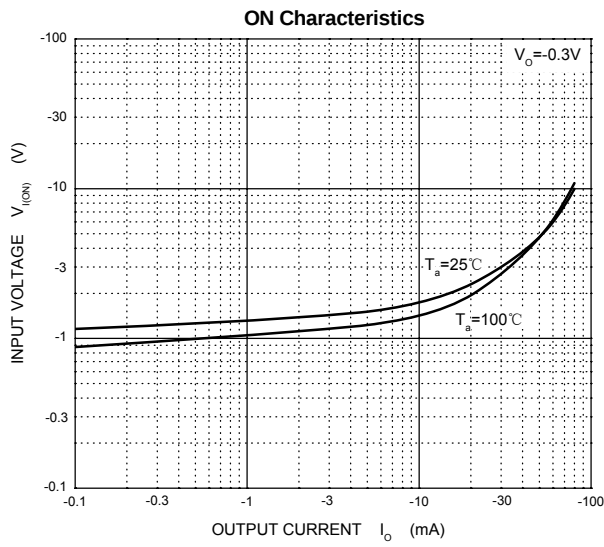
Note 1: 150mW per element must not be exceeded.

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Input voltage	$V_{I(off)}$	0.5			V	$V_{CC}=5V, I_O=100\mu A$
	$V_{I(on)}$			3		$V_O=0.3V, I_O=10mA$
Output voltage	$V_{O(on)}$			0.3	V	$I_O/I_I=10mA/0.5mA$
Input current	I_I			0.88	mA	$V_I=5V$
Output current	$I_{O(off)}$			0.5	μA	$V_{CC}=50V, V_I=0$
DC current gain	G_I	30				$V_O=5V, I_O=5mA$
Input resistance	R_I	7	10	13	k Ω	
Resistance ratio	R_2/R_1	0.8	1	1.2		
Transition frequency	f_T		250		MHz	$V_{CE}=10V, I_E=-5mA, f=100MHz$

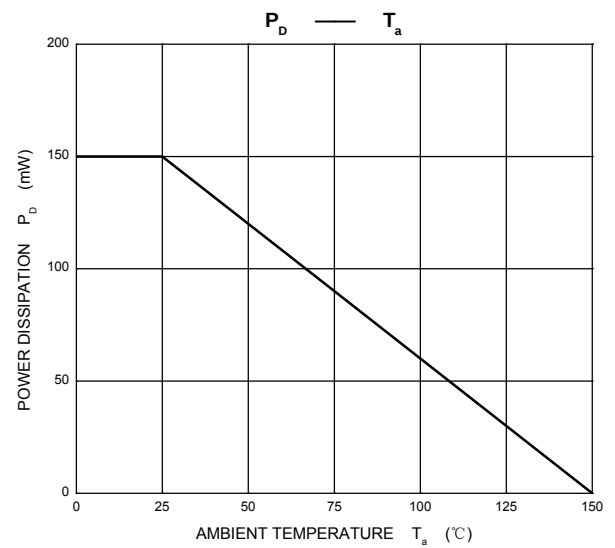
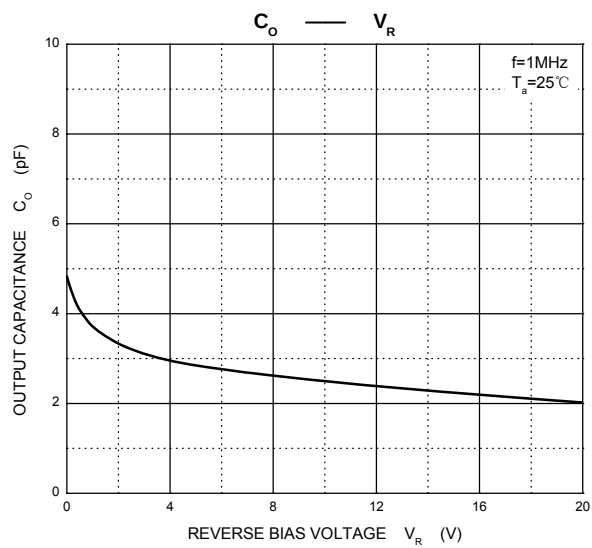
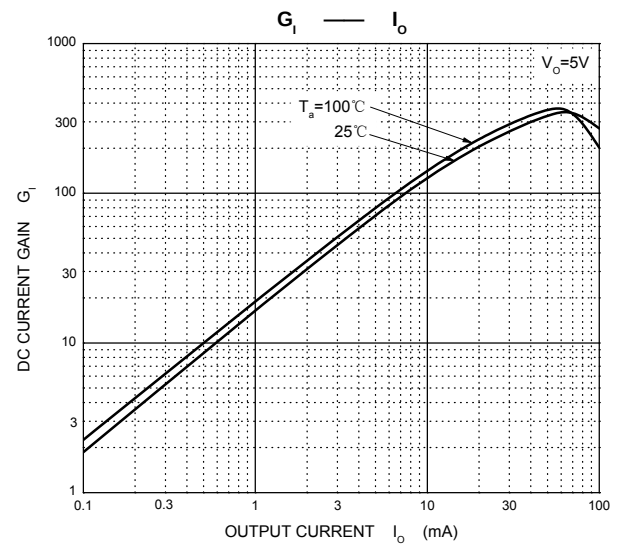
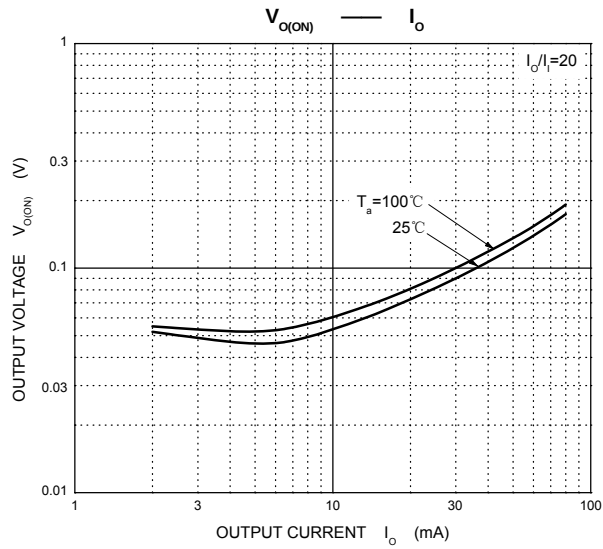
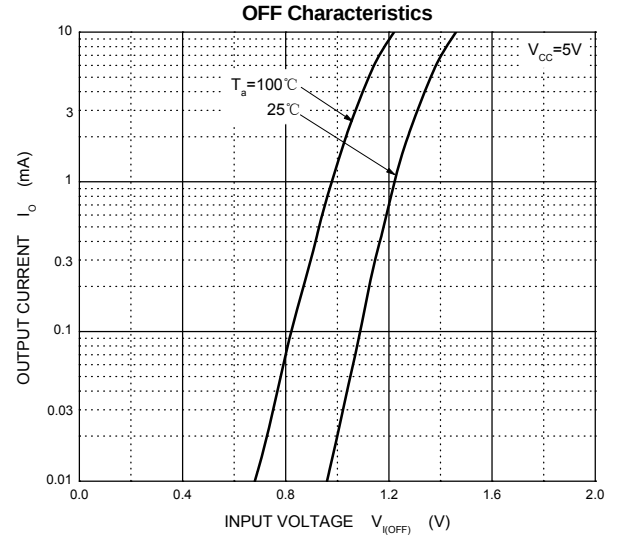
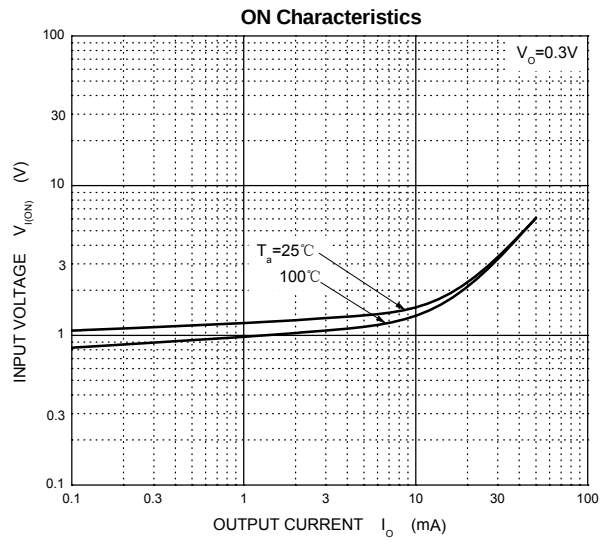
Typical Characteristics

DTA114E

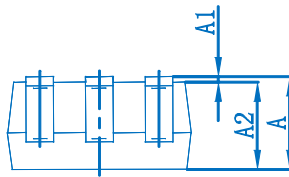
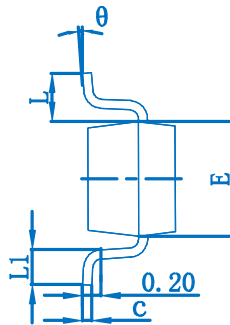
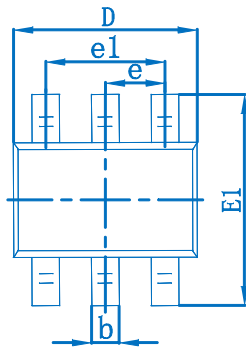


Typical Characteristics

DTC114E

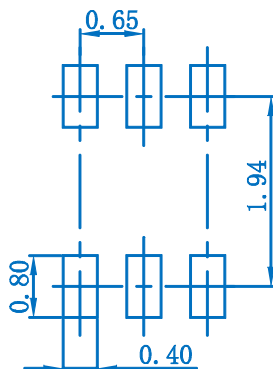


SOT-363 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

SOT-363 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.